

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	METHOD OF FORMING STRAINED SI/SIGE ON INSULATOR WITH SILICON GERMANIUM BUFFER						
Application Number:	10/710,255						
Confirmation Number:	6/29/04						
First Named Applicant:	Huajie Chen						
Attorney Docket Number:	FIS920030381US1						
Art Unit:	2813						
Examiner:							
Search string:	(6603156 or 6524935).pn						
US Patent Documents							
Note: Applicant is not required to submit a paper copy of cited US Patent Documents							
Init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
CC	1	6603156	2003-08-05	Rim	B2	257	190
CC	2	6524935	2003-02-25	Canaperi, et al.	B1	438	458
Signature							
Examiner Name				Date			
Chandra Chaudhari				1-05			